

## 1. General description

Silicon Carbide Schottky diode in a TO263 (D2PAK) plastic package, designed for high frequency switched-mode power supplies.

## 2. Features and benefits

- Highly stable switching performance
- High forward surge capability  $I_{FSM}$
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

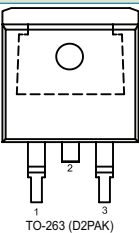
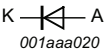
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
<b>Absolute maximum rating</b>						
$V_{RRM}$	repetitive peak reverse voltage		650			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 112$ °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	10			A
$T_j$	junction temperature		175			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; <a href="#">Fig. 5</a>	-	1.5	1.7	V
		$I_F = 10$ A; $T_j = 150$ °C; <a href="#">Fig. 5</a>	-	1.8	2.1	V
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 10$ A; $di_F/dt = 500$ A/ $\mu$ s; $V_R = 400$ V; $T_j = 25$ °C; <a href="#">Fig. 7</a>	-	16	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		
2	K	cathode [1]		
3	A	anode		
mb	K	mounting base; connected to cathode		

[1] It is not possible to connect to pin 2 of the TO263 package.

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
GKTSC10650B	TO263	GKTSC10650B6J	Reel	800	TO263N	16-Sep-2015

## 7. Marking

Table 4. Marking codes

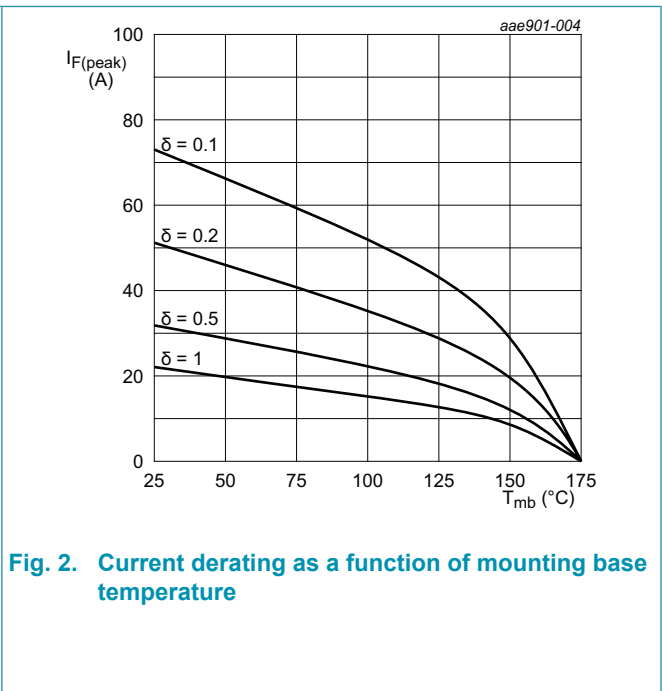
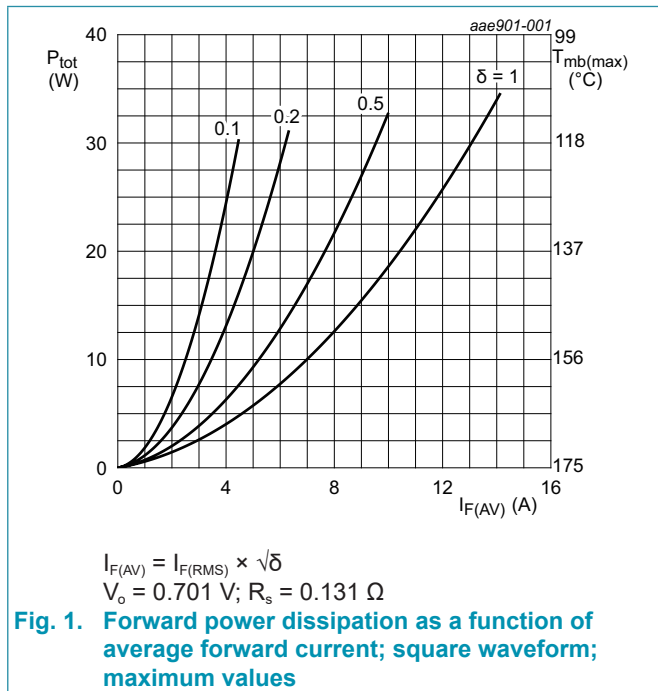
Type number	Marking codes
GKTSC10650B	GKTSC 10650B

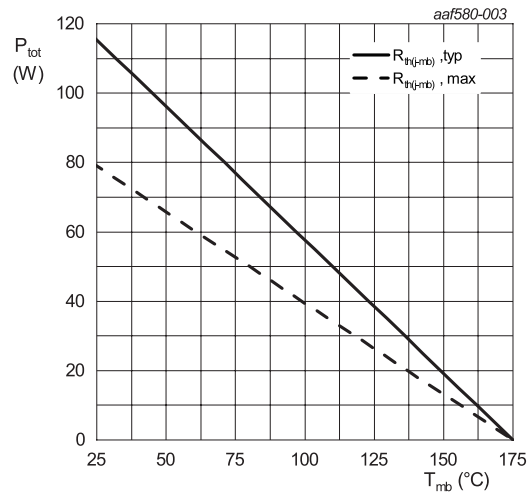
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		650	V
$V_{RWM}$	crest working reverse voltage		650	V
$V_R$	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 112\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	10	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_{mb} \leq 112\text{ }^\circ\text{C}$ ; square-wave pulse	20	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse	50	A
		$t_p = 10\text{ }\mu\text{s}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; square-wave pulse	450	A
$I^2t$	$I^2t$ for fusing	sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$	12.5	$\text{A}^2\text{s}$
$T_{stg}$	storage temperature		-55 to 175	$^\circ\text{C}$
$T_j$	junction temperature		175	$^\circ\text{C}$





**Fig. 3. Total power dissipation as a function of mounting base temperature**

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; <a href="#">Fig. 4</a>	-	1.3	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

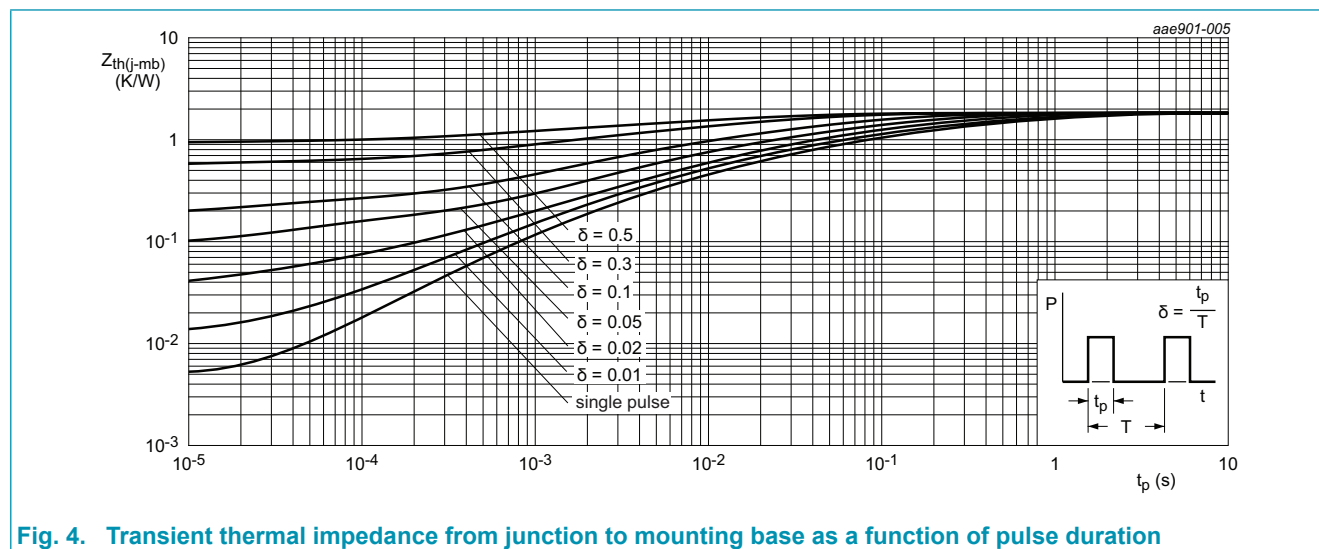
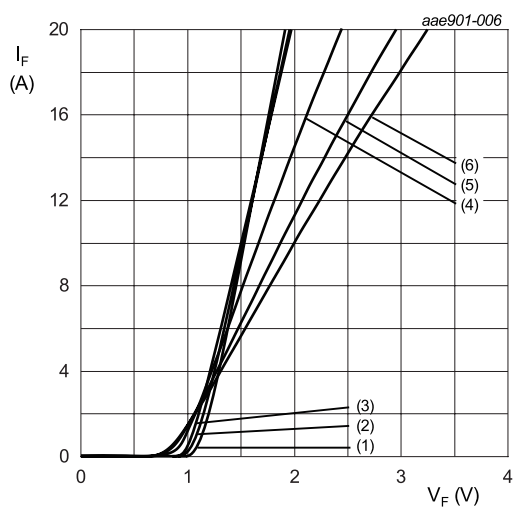


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_F$	forward current	$I_F = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 5}$	-	1.5	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C}; \text{ Fig. 5}$	-	1.8	2.1	V
$I_R$	reverse current	$V_R = 650 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 6}$	-	-	60	$\mu\text{A}$
		$V_R = 650 \text{ V}; T_j = 150 \text{ }^\circ\text{C}; \text{ Fig. 6}$	-	-	240	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; di_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{ Fig. 7}$	-	16	-	nC
$C_d$	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	328	-	pF
		$f = 1 \text{ MHz}; V_R = 300 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	44	-	pF
		$f = 1 \text{ MHz}; V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	42	-	pF
$E_{as}$	non-repetitive avalanche energy	$I_R = 5.5 \text{ A}; L = 5 \text{ mH}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$	75	-	-	mJ



$V_o = 0.701 \text{ V}; R_s = 0.131 \Omega$   
 (1)  $T_j = -55 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 0 \text{ }^\circ\text{C}$ ; typical values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; typical values  
 (4)  $T_j = 100 \text{ }^\circ\text{C}$ ; typical values  
 (5)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values  
 (6)  $T_j = 175 \text{ }^\circ\text{C}$ ; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

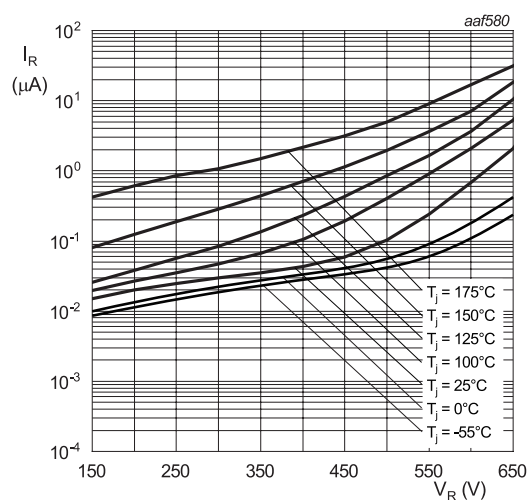
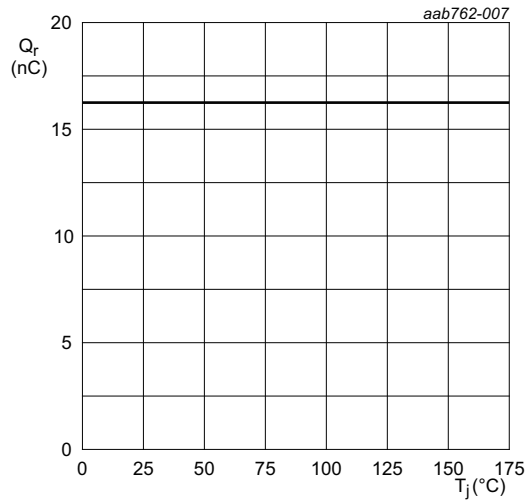


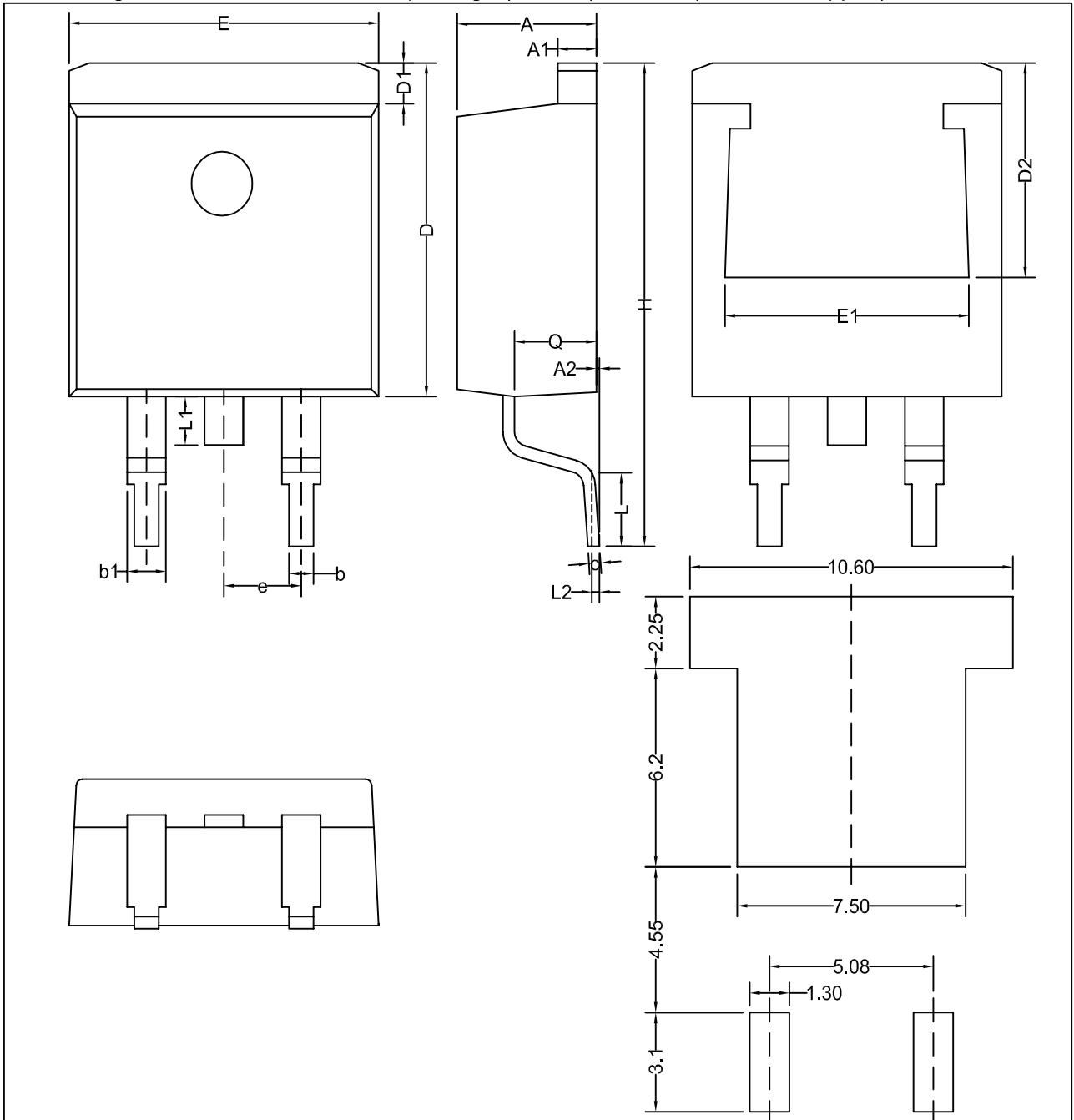
Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



**Fig. 7. Recovered charge as a function of junction temperature**

**11. Package outline**

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



Recommended Footprint

Unit	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---	---	10.30	---	15.80	2.90	1.75	---	2.79

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